

HSU276

Silicon Schottky Barrier Diode for Detector and Mixer

REJ03G0141-0700Z
(Previous: ADE-208-078F)
Rev.7.00
Nov.10.2003

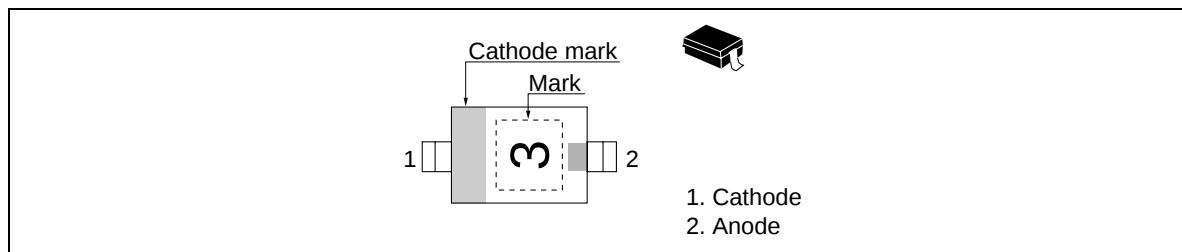
Features

- High forward current, Low capacitance.
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSU276	3	URP

Pin Arrangement



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V _R	3	V
Average rectified current	I _O	30	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	–55 to +125	°C

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V _R	3	—	—	V	I _R = 1 mA
Reverse current	I _R	—	—	50	μA	V _R = 0.5 V
Forward current	I _F	35	—	—	mA	V _F = 0.5 V
Capacitance	C	—	—	0.85	pF	V _R = 0.5 V, f = 1 MHz
ESD-Capability ^{*1}	—	30	—	—	V	C = 200 pF, R = 0 Ω, Both forward and reverse direction 1 pulse.

Note: 1. Failure criterion ; I_R ≥ 100 μA at V_R = 0.5 V

Main Characteristics

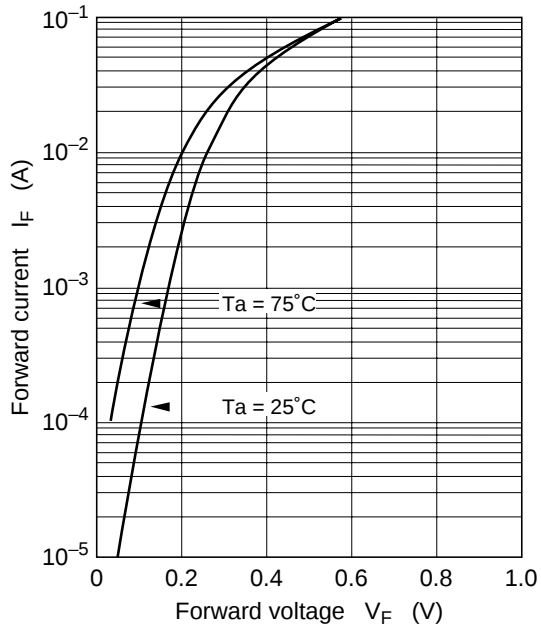


Fig.1 Forward current vs. Forward voltage

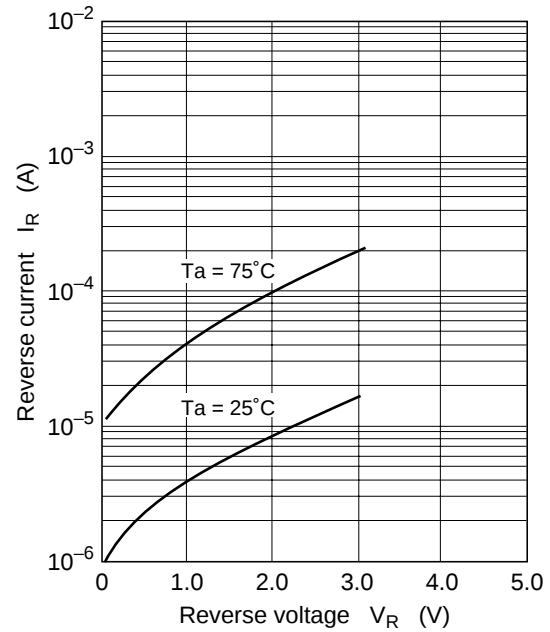


Fig.2 Reverse current vs. Reverse voltage

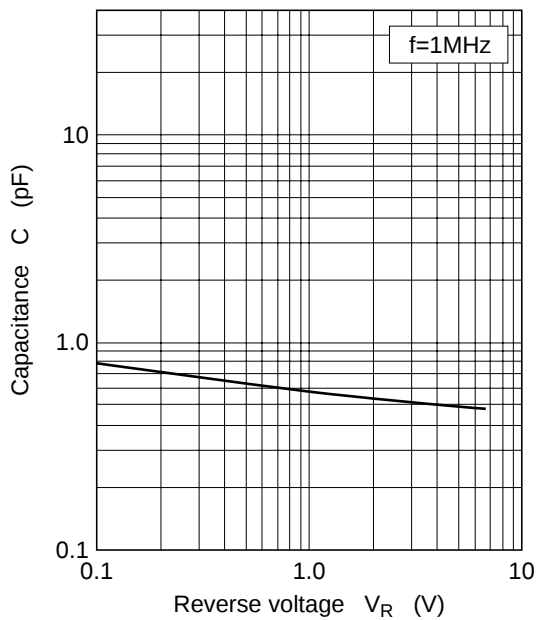
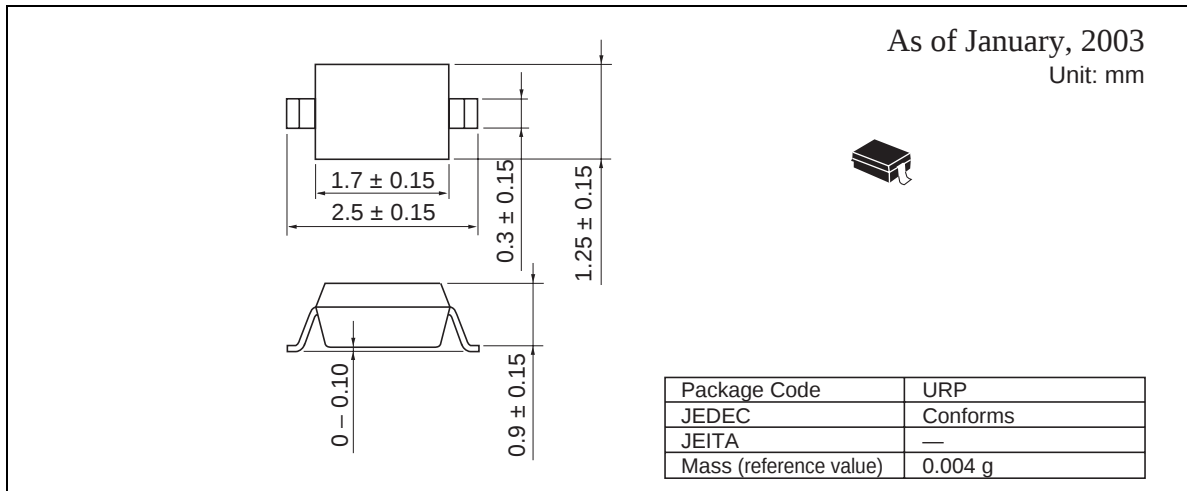


Fig.3 Capacitance vs. Reverse voltage

Package Dimensions



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